

8A, 500V N-CHANNEL MOSFET

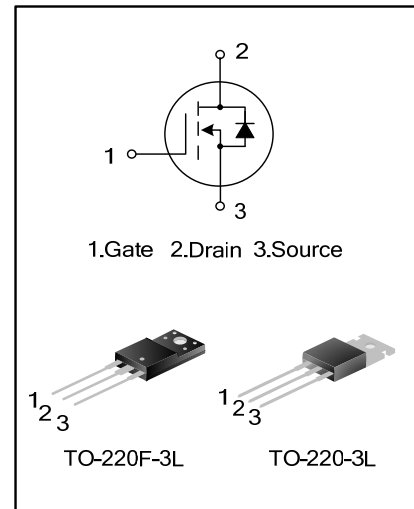
GENERAL DESCRIPTION

SVD840T/F is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary S-Rin™ structure VDMOS technology. The improved planar stripe cell and the improved guard ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

FEATURES

- * 8A,500V, $R_{DS(on)}$ (typ) = $0.62\Omega @ V_{GS}=10V$
- * Low gate charge
- * Low C_{rss}
- * Fast switching
- * Improved dv/dt capability



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SVD840T	TO-220-3L	SVD840T	Pb free	Tube
SVD840F	TO-220F-3L	SVD840F	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_c=25°C unless otherwise noted)

Characteristics	Symbol	Rating		Unit
		SVD840T	SVD840F	
Drain-Source Voltage	V _{DS}	500		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current	I _D	8.0		A
Drain Current Pulsed	I _{DM}	32		A
Power Dissipation(TC=25°C, TO-220 Package) -Derate above 25°C	P _D	135	49	W
		1.08	0.39	W/°C
Single Pulsed Avalanche Energy (Note 1)	E _{AS}	686		mJ
Operation Junction Temperature	T _J	150		°C
Storage Temperature	T _{stg}	-55~+150		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Rating		Unit
		SVD840T	SVD840F	
Thermal Resistance, Junction-to-Case	R _{θJC}	0.93	2.56	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	120	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _D =250μA	500	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	--	--	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =4.0A	--	0.62	0.9	Ω
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	--	1100	--	pF
Output Capacitance	C _{oss}		--	115	--	
Reverse Transfer Capacitance	C _{rss}		--	5	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} =250V, I _D =8.0A, R _G =25Ω (Note 2,3)	--	34	--	ns
Turn-on Rise Time	t _r		--	24	--	
Turn-off Delay Time	t _{d(off)}		--	208	--	
Turn-off Fall Time	t _f		--	31	--	
Total Gate Charge	Q _g	V _{DS} =400V, I _D =8.0A, V _{GS} =10V (Note 2,3)	--	31	--	nC
Gate-Source Charge	Q _{gs}		--	5.6	--	
Gate-Drain Charge	Q _{gd}		--	12	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I _S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	8.0	A
Pulsed Source Current	I _{SM}		--	--	32	
Diode Forward Voltage	V _{SD}	I _S =8.0A, V _{GS} =0V	--	--	1.5	V
Reverse Recovery Time	T _{rr}	I _S =8.0A, V _{GS} =0V, dI _F /dt=100A/μS (Note 2)	--	270	--	ns
Reverse Recovery Charge	Q _{rr}		--	1.89	--	μC

Notes:

1. L=30mH, I_{AS}=5.76A, V_{DD}=188V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

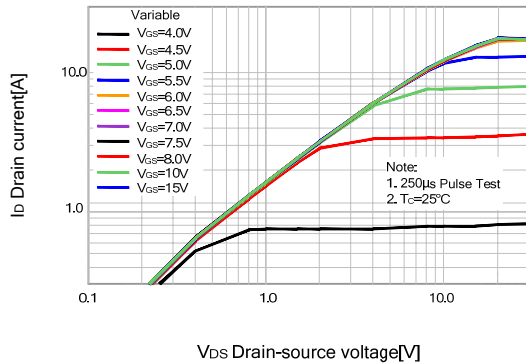


Figure 2. Transfer Characteristics

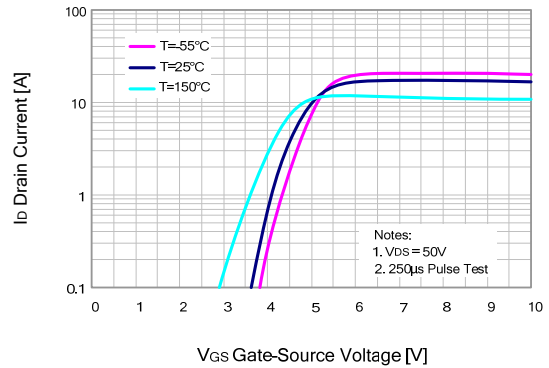


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

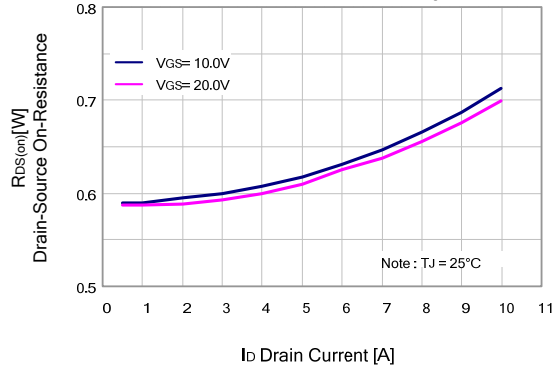


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

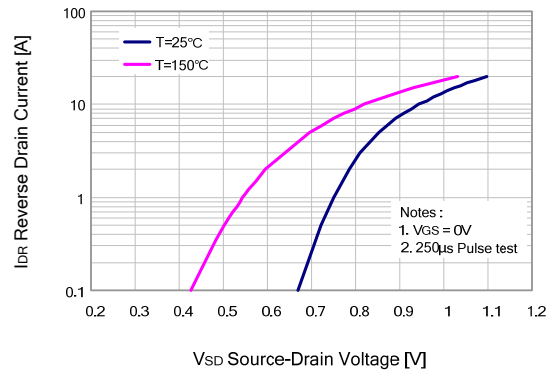


Figure 5. Capacitance Characteristics

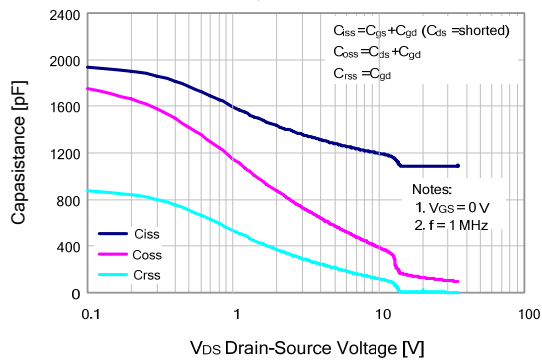
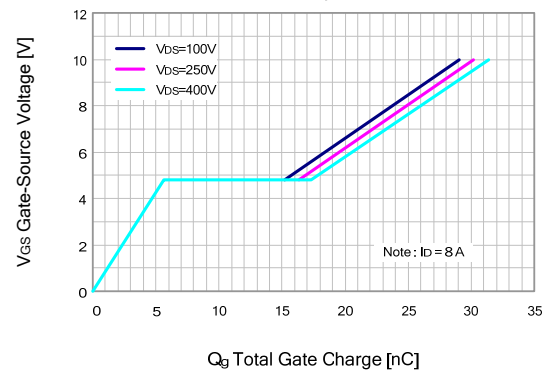


Figure 6. Gate Charge Characteristics



TYPICAL CHARACTERISTICS (continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

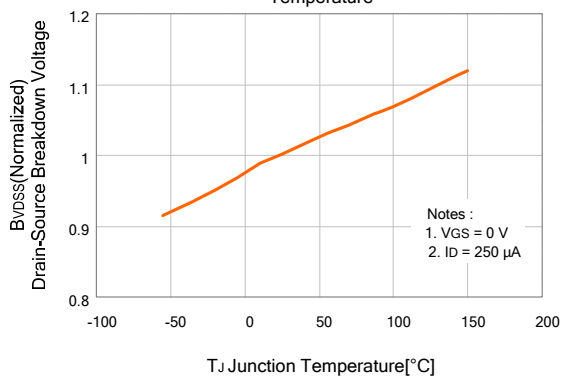


Figure 8. On-resistance Variation vs Temperature

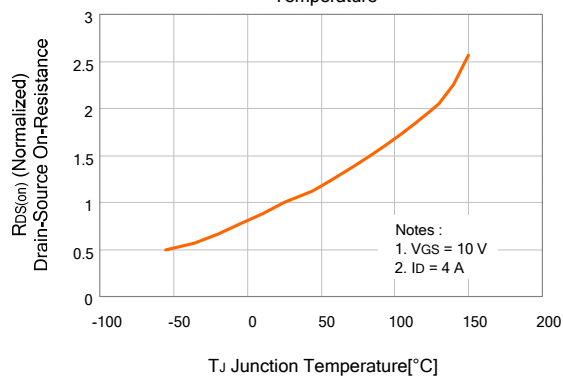


Figure 9-1. Max. Safe Operating Area(SVD840T)

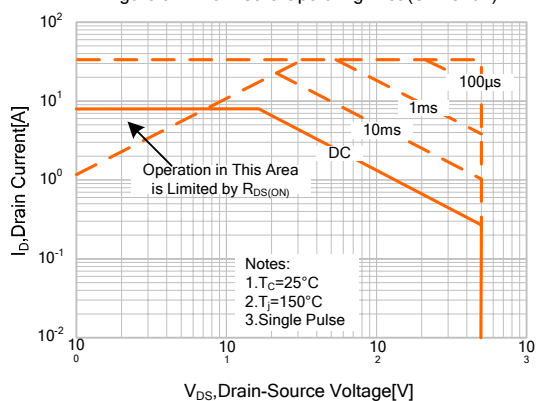


Figure 9-2. Max. Safe Operating Area(SVD840F)

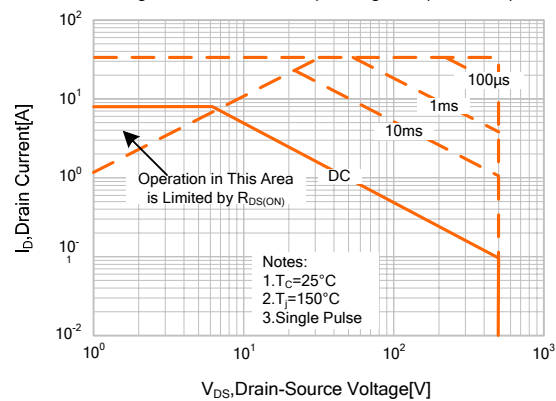
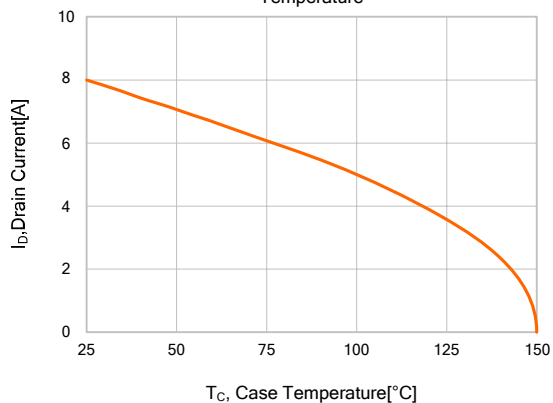
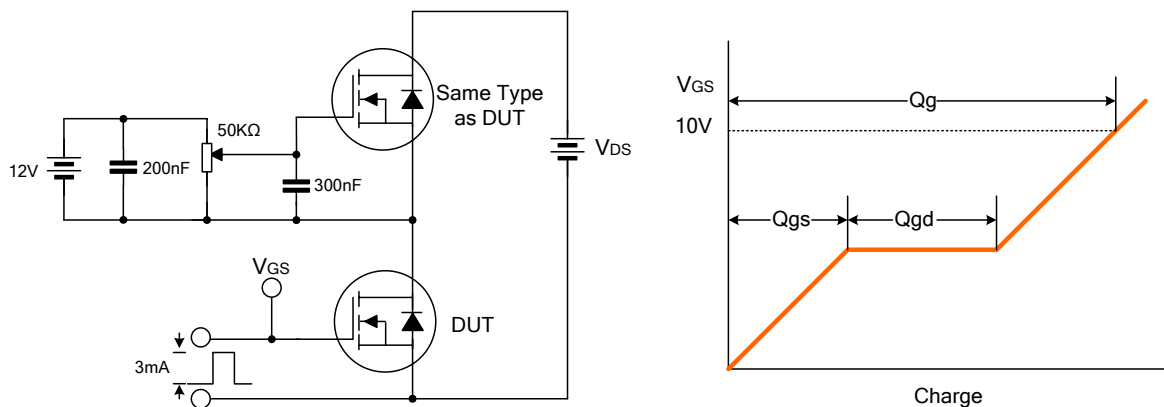


Figure 10. Maximum Drain Current vs. Case Temperature

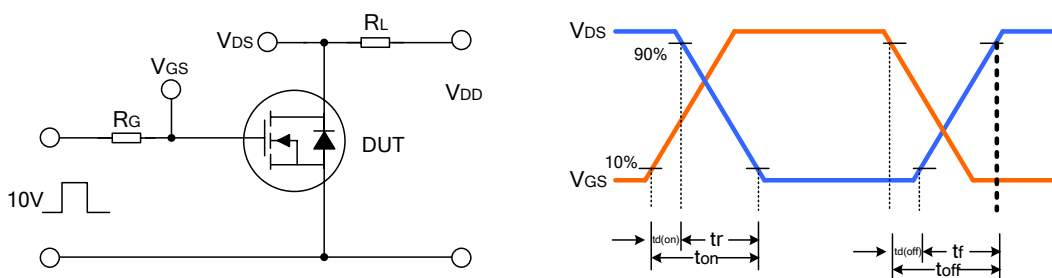


TYPICAL TEST CIRCUIT

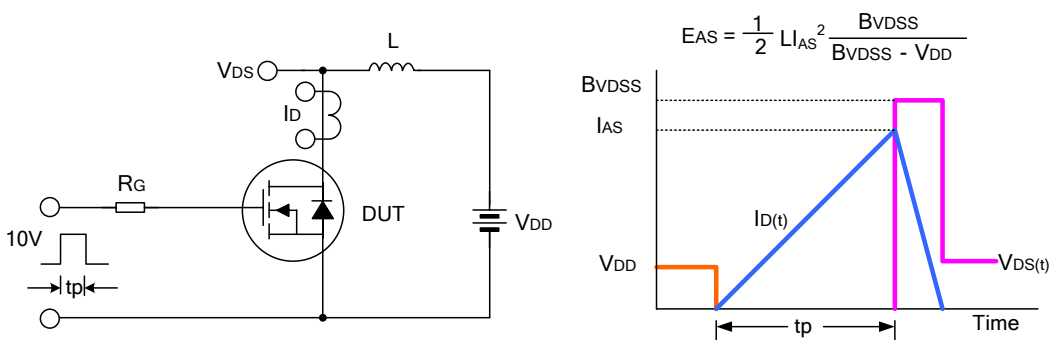
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



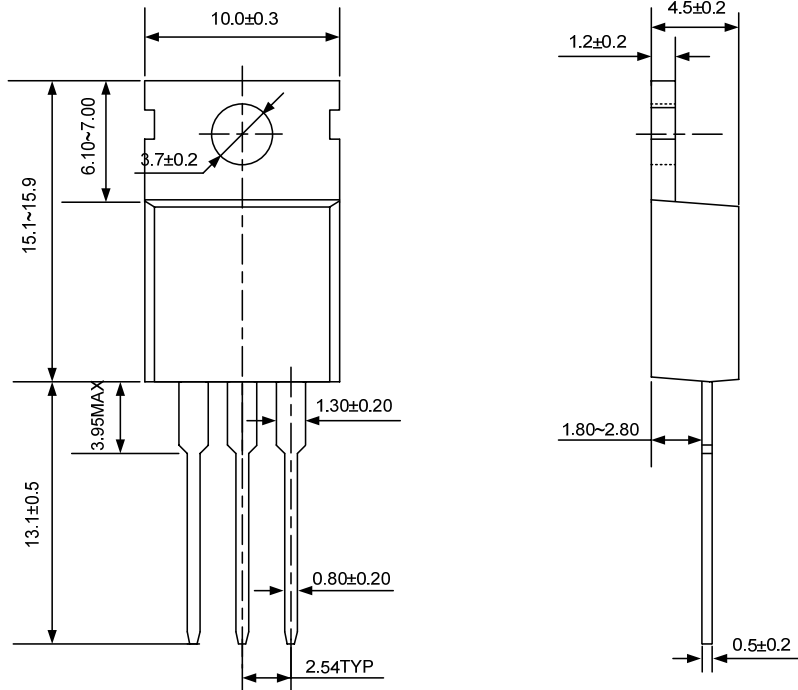
Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE

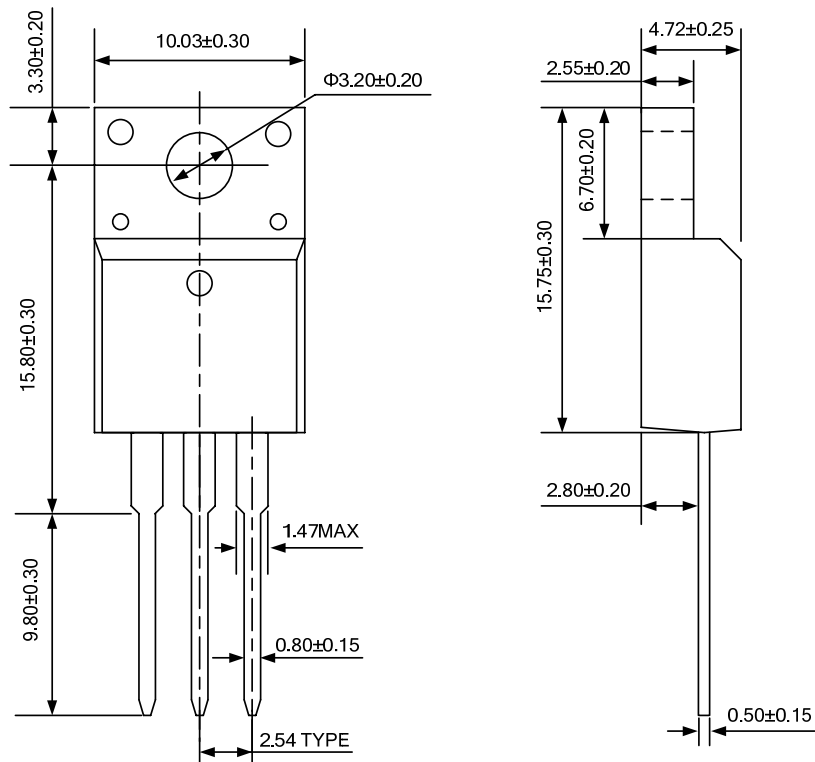
TO-220-3L

UNIT: mm



TO-220F-3L

UNIT: mm



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- Silan will supply the best possible product for customers!

ATTACHMENT**Revision History**

Date	REV	Description	Page
2010.05.24	1.0	Original	
2010.08.24	1.1	Modify the value of PD, Thermal Resistance, Junction-to-Case; Add SOA and ID-TC	
2010.10.15	1.2	Modify "TYPICAL CHARACTERISTICS"	
2010.10.21	1.3	Modify the template of Datasheet	
2011.01.17	1.4	Modify "PACKAGE OUTLINE"	